H-Cell Halfcut Series





Physical Characteristics

Dimensions Diagonal	183.5mm X 183.5mm, ± 1% 256mm ± 10mm				
Thickness(Si)	130 μ m ± 80 μ m				
Front(+)	Alkaline texturized surface with silicon nitride anti-reflecting coating				
	16 X 0.036mm ± 0.05mm bus bars				
	Distance between bus bars : 10.8mm				
Back(-)	Alkaline texturized surface with silicon nitride anti-reflecting coating				
	Distance between hus bars - 10 8mm				





Features

- -High Cell-To- Module ratio through precise cell conversion efficiency sorting, classified efficiency grade by both minimum power and current.
- -Excellent electrical long-term stability and reliability by using of best raw materials and through strict quality inspection control.
- -Low breakage rate by using high gualified and stable wafers.
- -High quality homogeneous appearance by sorting into defined color classes.
- -100% screened for reverse current and shunt resistance.
- -The best solution for PV module with above 490W(6x20) and 590W(6x24) outputs.

Quality Control and Professional Service

- -Regular calibration of test equipment using Fraunhofer ISE reference cell. -Environmental friendly due to REACH-SVHC and RoHS compliances.
- -Professional on-site service and support for module certification.
- -Regular light source AAA class calibration for stable conversion efficiency. -Lowest LID by periodic monitoring and superior wafer incoming control.

Electrical Characteristi	cs		

Efficiency Code		255	254	253	252	251	250	249	248	247	246	245
Efficiency odde	E #2(0/)	25.50	25.40	25.20	25.20	25.10	25.00	24.00	24.80	24.70	24.60	24.50
Efficiency	ETT(%)	25.50	25.40	25.30	25.20	25.10	25.00	24.90	24.80	24.70	24.60	24.50
Power	Pmpp(W)	8.54	8.50	8.47	8.43	8.40	8.37	8.33	8.30	8.27	8.23	8.20
Max. Power Current	Impp(A)	13.334	13.327	13.310	13.270	13.244	13.226	13.196	13.172	13.148	13.125	13.104
Short Circuit Current	Isc(A)	13.888	13.887	13.881	13.876	13.866	13.866	13.865	13.865	13.864	13.863	13.863
Max. Power Voltage	Vmpp(V)	0.640	0.638	0.637	0.635	0.634	0.633	0.632	0.630	0.629	0.627	0.626
Open Circuit Voltage	Voc(V)	0.732	0.731	0.730	0.729	0.728	0.727	0.726	0.725	0.723	0.722	0.721

Standard test condition: AM1.5, 1000W/m², 25°c Average accuracy of all tests is +/-1.5% rel.

Temperature Coefficients

Current Temperature Coefficient	a(ISC)	0.0450%/K
Voltage Temperature Coefficient	B(VOC)	-0.2487%/K
Power Temperature Coefficient	γ(Pmax)	-0.2819%/K

Standard test condition: AM1.5, 1000W/m², 25°c

Processing Recommendations

Solder Joint

Copper ribbons coated with 15~25µm: 62%Sn/36%Pb/2%Ag or 60%Sn/40%Pb

Solderability

Peel Strength Minimum

>1.25 N/mm

Soldering results may differ due to different flux, ribbons, soldering methods, and parameters.







Typical IV-Power Curve



* All data measured under standard testing condition (STC): 1000 W/m², AM 1.5, 25 °C.

- * All figures bear ±2% tolerance. * Reference call are under testing by Fraun
- * Reference cell are under testing by Fraunhofer ISE in Freiburg.

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